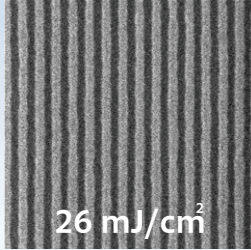


# JSR EUV Photoresist

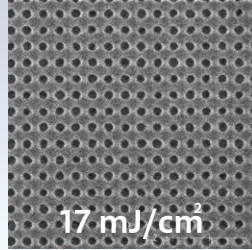
## Challenge for Sensitivity and Defectivity

15 nm L/S



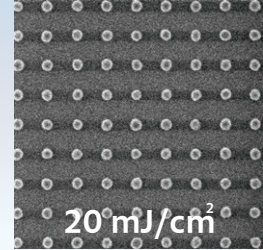
Substrate: Organic HM  
Resist FT: 35 nm

21 nm C/H

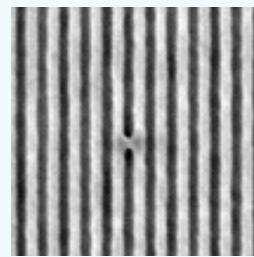
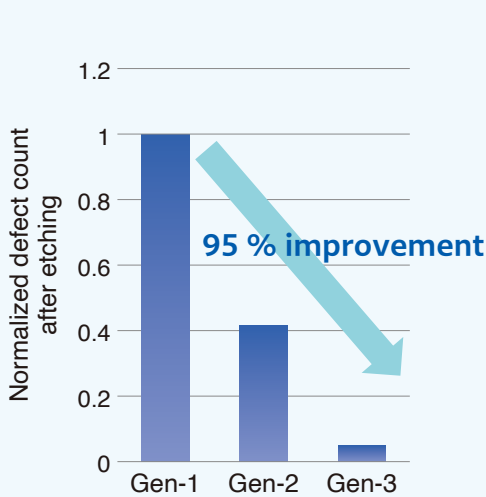


Substrate: ML/Organic HM  
Resist FT: 50 nm

21 nm Pillar



Substrate: ML/Organic HM  
Resist FT: 50 nm



Target CD: 18 nm LS  
Exposure: NXE3300 (NA0.33)



## Challenge for Next Generation Photoresist

**inpria Corporation**

Development and manufacturing of “metal-based EUV resists”

